

The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) A light emitting device comprising:
a thin film transistor on an insulating surface;
an interlayer insulating film over the thin film transistor;
an anode having a ~~leveling surface~~ first portion and a second portion over the interlayer insulating [[film]] film, wherein the first portion has a leveling surface;
a wiring electrically connected to the thin film transistor and the anode;
a bank over the wiring and [[a]] the second portion of the anode;
~~a first~~ an insulating film over the leveling surface of [[anode]] the first portion and an upper surface of the bank;
an organic compound layer over the anode with the [[first]] insulating film interposed therebetween; and
a cathode over the organic compound layer.

2. (Currently Amended) A light emitting device comprising:
a thin film transistor on an insulating surface;
an interlayer insulating film over the thin film transistor;
an anode having a ~~leveling surface~~ first portion and a second portion over the interlayer insulating [[film]] film, wherein the first portion has a leveling surface;
a wiring electrically connected to the thin film transistor and the anode;
a bank over the wiring and a portion of the anode;
~~a first~~ an insulating film over the leveling surface of the anode and an upper surface of the bank;

an organic compound layer over the anode with the [[first]] insulating film interposed therebetween; and

a cathode over the organic compound layer,

wherein the [[first]] insulating film is formed from an organic resin film.

3. (Currently Amended) A light emitting device comprising:

a thin film transistor on an insulating surface;

an interlayer insulating film over the thin film transistor;

an anode having a ~~leveling surface~~ first portion and a second portion over the interlayer insulating [[film]] film, wherein the first portion has a leveling surface;

a wiring electrically connected to the thin film transistor and the anode;

a bank over the wiring and a portion of the anode;

~~a~~ first an insulating film over the leveling surface of the anode and an upper surface of the bank;

an organic compound layer over the anode with the [[first]] insulating film interposed therebetween; and

a cathode over the organic compound layer,

wherein the [[first]] insulating film is at a film thickness of 1 to 5nm.

4. (Canceled)

5. (Currently Amended) A light emitting device comprising:

a thin film transistor on an insulating surface;

an interlayer insulating film over the thin film transistor;

an anode having a ~~leveling surface~~ first portion and a second portion over the interlayer insulating [[film]] film, wherein the first portion has a leveling surface;

a wiring electrically connected to the thin film transistor and the anode;

a bank over the wiring and a portion of the anode;

~~a~~first ~~an~~ insulating film over the leveling surface of the anode and an upper surface of the bank;

an organic compound layer over the anode with the ~~[[first]]~~ insulating film interposed therebetween; and

a cathode over the organic compound layer,

wherein the anode is formed from indium tin oxide.

6. (Currently Amended) A light emitting device comprising:

a thin film transistor on an insulating surface;

an interlayer insulating film over the thin film transistor;

an anode having a leveling surface ~~first portion and a second portion~~ over the interlayer insulating ~~[[film]]~~ film, wherein the first portion has a leveling surface;

a wiring electrically connected to the thin film transistor and the anode;

a bank over the wiring and a portion of the anode;

~~a~~first ~~an~~ insulating film over the leveling surface of the anode and an upper surface of the bank;

an organic compound layer over the anode with the ~~[[first]]~~ insulating film interposed therebetween; and

a cathode over the organic compound layer; layer,

wherein the ~~[[first]]~~ insulating film is formed from an organic resin ~~[[film;]]~~ film,

wherein the ~~[[first]]~~ insulating film is at a film thickness of 1 to ~~[[5nm;]]~~ 5nm, and

wherein the anode is formed from indium tin oxide.

7. (Original) A device according to claim 1, wherein an average surface roughness (Ra) of the anode is in a range of 0.9 nm or less.

8. (Original) A device according to claim 1, wherein an average surface roughness (Ra) of the anode is in a range of 0.85 nm or less.

9. (Original) A device according to claim 1, wherein the interlayer insulating film comprises at least one selected from the group consisting of a silicon oxide film, a silicon nitride oxide film and a silicon oxide nitride film.

10. (Original) A device according to claim 1,
wherein the bank is processed by a plasma; and
wherein the bank comprises a hardened film including at least an element selected from the group consisting of hydrogen, nitrogen, halocarbon, hydrogen fluoride, and noble gas.

11. (Withdrawn) A device according to claim 1,
wherein a second insulating film is formed over the interlayer insulating film; and
wherein the second insulating film comprises at least one selected from the group consisting of a silicon nitride film and a diamond like carbon film.

12. (Original) A device according to claim 1,
wherein the light emitting device is in combination with an electric device; and
wherein the electric device is one selected from the group consisting of a display, a digital still camera, a notebook type personal computer, a mobile computer, an image reproduction apparatus including a recording medium, a goggle type display, a video camera and a mobile phone.

13. (Original) A device according to claim 2, wherein an average surface roughness (Ra) of the anode is in a range of 0.9 nm or less.

14. (Original) A device according to claim 2, wherein an average surface roughness (Ra) of the anode is in a range of 0.85 nm or less.

15. (Original) A device according to claim 2, wherein the interlayer insulating film comprises at least one selected from the group consisting of a silicon oxide film, a silicon nitride oxide film and a silicon oxide nitride film.

16. (Original) A device according to claim 2,
wherein the bank is processed by a plasma; and
wherein the bank comprises a hardened film including at least an element selected from the group consisting of hydrogen, nitrogen, halocarbon, hydrogen fluoride, and noble gas.

17. (Withdrawn) A device according to claim 2,
wherein a second insulating film is formed over the interlayer insulating film; and
wherein the second insulating film comprises at least one selected from the group consisting of a silicon nitride film and a diamond like carbon film.

18. (Original) A device according to claim 2,
wherein the light emitting device is in combination with an electric device; and
wherein the electric device is one selected from the group consisting of a display, a digital still camera, a notebook type personal computer, a mobile computer, an image reproduction apparatus including a recording medium, a goggle type display, a video camera and a mobile phone.

19. (Original) A device according to claim 3, wherein an average surface roughness (Ra) of the anode is in a range of 0.9 nm or less.

20. (Original) A device according to claim 3, wherein an average surface roughness (Ra) of the anode is in a range of 0.85 nm or less.

21. (Original) A device according to claim 3, wherein the interlayer insulating film comprises at least one selected from the group consisting of a silicon oxide film, a silicon nitride oxide film and a silicon oxide nitride film.

22. (Original) A device according to claim 3,
wherein the bank is processed by a plasma; and
wherein the bank comprises a hardened film including at least an element selected from the group consisting of hydrogen, nitrogen, halocarbon, hydrogen fluoride, and noble gas.

23. (Withdrawn) A device according to claim 3,
wherein a second insulating film is formed over the interlayer insulating film; and
wherein the second insulating film comprises at least one selected from the group consisting of a silicon nitride film and a diamond like carbon film.

24. (Original) A device according to claim 3,
wherein the light emitting device is in combination with an electric device; and
wherein the electric device is one selected from the group consisting of a display, a digital still camera, a notebook type personal computer, a mobile computer, an image reproduction apparatus including a recording medium, a goggle type display, a video camera and a mobile phone.

25.-30. (Canceled)

31. (Original) A device according to claim 5, wherein an average surface roughness (Ra) of the anode is in a range of 0.9 nm or less.

32. (Original) A device according to claim 5, wherein an average surface roughness (Ra) of the anode is in a range of 0.85 nm or less.

33. (Original) A device according to claim 5, wherein the interlayer insulating film comprises at least one selected from the group consisting of a silicon oxide film, a silicon nitride oxide film and a silicon oxide nitride film.

34. (Original) A device according to claim 5,
wherein the bank is processed by a plasma; and
wherein the bank comprises a hardened film including at least an element selected from the group consisting of hydrogen, nitrogen, halocarbon, hydrogen fluoride, and noble gas.

35. (Withdrawn) A device according to claim 5,
wherein a second insulating film is formed over the interlayer insulating film; and
wherein the second insulating film comprises at least one selected from the group consisting of a silicon nitride film and a diamond like carbon film.

36. (Original) A device according to claim 5,
wherein the light emitting device is in combination with an electric device; and
wherein the electric device is one selected from the group consisting of a display, a digital still camera, a notebook type personal computer, a mobile computer, an image reproduction apparatus including a recording medium, a goggle type display, a video camera and a mobile phone.

37. (Original) A device according to claim 6, wherein an average surface roughness (Ra) of the anode is in a range of 0.9 nm or less.

38. (Original) A device according to claim 6, wherein an average surface roughness (Ra) of the anode is in a range of 0.85 nm or less.

39. (Original) A device according to claim 6, wherein the interlayer insulating film comprises at least one selected from the group consisting of a silicon oxide film, a silicon nitride oxide film and a silicon oxide nitride film.

40. (Original) A device according to claim 6,
wherein the bank is processed by a plasma; and
wherein the bank comprises a hardened film including at least an element selected from the group consisting of hydrogen, nitrogen, halocarbon, hydrogen fluoride, and noble gas.

41. (Withdrawn) A device according to claim 6,
wherein a second insulating film is formed over the interlayer insulating film; and
wherein the second insulating film comprises at least one selected from the group consisting of a silicon nitride film and a diamond like carbon film.

42. (Original) A device according to claim 6,
wherein the light emitting device is in combination with an electric device; and
wherein the electric device is one selected from the group consisting of a display, a digital still camera, a notebook type personal computer, a mobile computer, an image reproduction apparatus including a recording medium, a goggle type display, a video camera and a mobile phone.

43. (Previously Presented) A device according to claim 1,
wherein the bank is formed from a resin insulating film.

44. (Previously Presented) A device according to claim 2,
wherein the bank is formed from a resin insulating film.

45. (Previously Presented) A device according to claim 3,
wherein the bank is formed from a resin insulating film.

46. (Previously Presented) A device according to claim 5,
wherein the bank is formed from a resin insulating film.

47. (Previously Presented) A device according to claim 6,
wherein the bank is formed from a resin insulating film.

48. (Previously Presented) A device according to claim 1,
wherein the leveling surface of the anode is formed by a wiping process using a
porous material.

49. (Previously Presented) A device according to claim 2,
wherein the leveling surface of the anode is formed by a wiping process using a
porous material.

50. (Previously Presented) A device according to claim 3,
wherein the leveling surface of the anode is formed by a wiping process using a
porous material.

51. (Previously Presented) A device according to claim 5,
wherein the leveling surface of the anode is formed by a wiping process using a
porous material.

52. (Previously Presented) A device according to claim 6,
wherein the leveling surface of the anode is formed by a wiping process using a
porous material.